CY7C1041BV33

256K x 16 Static RAM

Features

- **High speed**
  - **— t_{AA} = 12 ns**
- **Low active power**
  - **— 612 mW (max.)**
- **Low CMOS standby power (Commercial L version)**
  - **— 1.8 mW (max.)**
- **2.0V Data Retention (600 µW at 2.0V retention)**
- **Automatic power-down when deselected**
- **TTL-compatible inputs and outputs**
- **Easy memory expansion with CE and OE features**

Functional Description

The CY7C1041BV33 is a high-performance CMOS Static RAM organized as 262,144 words by 16 bits.

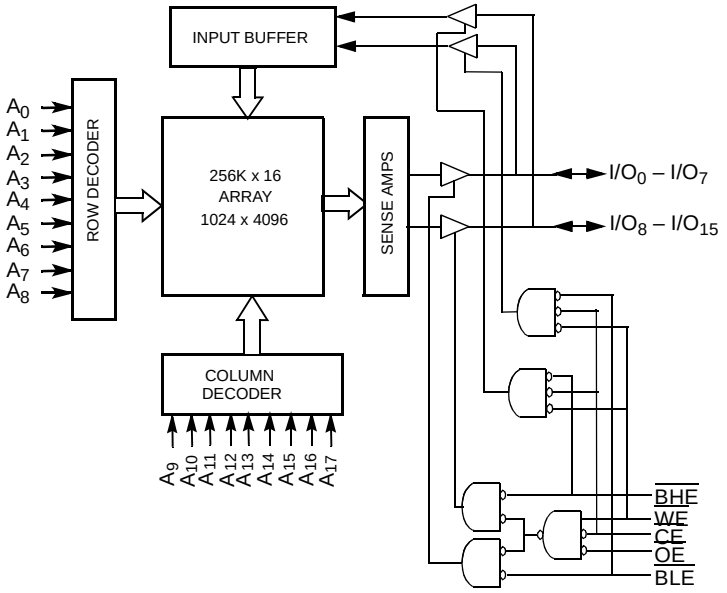
Writing to the device is accomplished by taking Chip Enable (CE) and Write Enable (WE) inputs LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{17}). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

Reading from the device is accomplished by taking Chip Enable (CE) and Output Enable (OE) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable (BHE) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this data sheet for a complete description of read and write modes.

The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when the device is deselected (CE HIGH), the outputs are disabled (OE HIGH), the BHE and BLE are disabled (BHE, BLE HIGH), or during a write operation (CE LOW, and WE LOW).

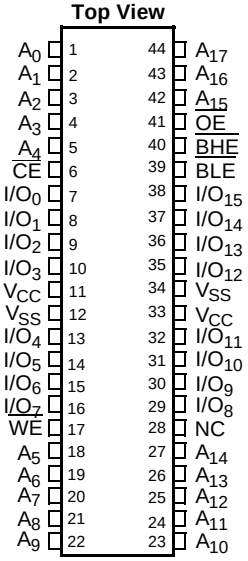
The CY7C1041BV33 is available in a standard 44-pin 400-mil-wide body width SOJ and 44-pin TSOP II package with center power and ground (revolutionary) pinout.

Logic Block Diagram



Pin Configuration

SOJ
TSOP II
Top View



Selection Guide

			-12	-15	-17	-20	-25
Maximum Access Time (ns)			12	15	17	20	25
Maximum Operating Current (mA)	Comm'l		190	170	160	150	130
	Ind'l		-	190	180	170	150
Maximum CMOS Standby Current (mA)	Com'l/Ind'l		8	8	8	8	8
	Com'l	L	0.5	0.5	0.5	0.5	0.5

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied..... –55°C to +125°C

Supply Voltage on V_{CC} to Relative GND[1] .... –0.5V to +4.6V

DC Voltage Applied to Outputs in High Z State[1]..... –0.5V to V_{CC} + 0.5V

DC Input Voltage[1] ..... –0.5V to V_{CC} + 0.5V

Current into Outputs (LOW) ..... 20 mA

Operating Range

Range	Ambient Temperature[2]	V_{CC}
Commercial	0°C to +70°C	3.3V ± 0.3V
Industrial	–40°C to +85°C	

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions			-12		-15		Unit
					Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA			2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA				0.4		0.4	V
V_{IH}	Input HIGH Voltage				2.2	V_{CC} + 0.5	2.2	V_{CC} + 0.5	V
V_{IL}	Input LOW Voltage[1]				–0.5	0.8	–0.5	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}			–1	+1	–1	+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ V_{CC}, Output Disabled			–1	+1	–1	+1	µA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., f = f_{MAX} = $1/t_{RC}$	Comm'l			190		170	mA
			Ind'l			-		190	mA
I_{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH} V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}				40		40	mA
I_{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f = 0	Com'l/Ind'l			8		8	mA
			Com'l	L		0.5		0.5	mA

Notes:

1. V_{IL} (min.) = –2.0V for pulse durations of less than 20 ns.
2. T_A is the "Instant On" case temperature.

Electrical Characteristics Over the Operating Range (continued)

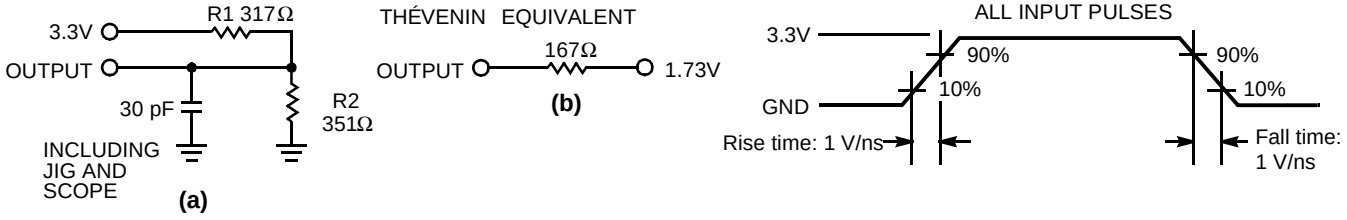
Parameter	Description	Test Conditions			-17 Min.	-17 Max.	-20 Min.	-20 Max.	-25 Min.	-25 Max.	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA			2.4		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA				0.4		0.4		0.4	V
V_{IH}	Input HIGH Voltage				2.2	V_{CC} + 0.5	2.2	V_{CC} + 0.5	2.2	V_{CC} + 0.5	V
V_{IL}	Input LOW Voltage[1]				–0.5	0.8	–0.5	0.8	–0.5	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}			–1	+1	–1	+1	–1	+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ V_{CC}, Output Disabled			–1	+1	–1	+1	–1	+1	µA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., f = f_{MAX} = $1/t_{RC}$	Comm'l			160		150		130	mA
			Ind'l			180		170		150	
I_{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH} V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}				40		40		40	mA
I_{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f=0	Com'l/Ind'l			8		8		8	mA
			Com'l	L		0.5		0.5		0.5	mA

Capacitance[3]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 3.3V	8	pF
C_{OUT}	I/O Capacitance		8	pF

Note:
3. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



Switching Characteristics[4] Over the Operating Range

Parameter	Description	-12		-15		-17		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE								
t_{RC}	Read Cycle Time	12		15		17		ns
t_{AA}	Address to Data Valid		12		15		17	ns
t_{OHA}	Data Hold from Address Change	3		3		3		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		12		15		17	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		6		7		8	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z	0		0		0		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[5, 6]		6		7		7	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[6]	3		3		3		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[5, 6]		6		7		7	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		12		15		17	ns
t_{DBE}	Byte Enable to Data Valid		6		7		7	ns
t_{LZBE}	Byte Enable to Low Z	0		0		0		ns
t_{HZBE}	Byte Disable to High Z		6		7		8	ns
WRITE CYCLE[7, 8]								
t_{WC}	Write Cycle Time	12		15		17		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	10		12		12		ns
t_{AW}	Address Set-Up to Write End	10		12		12		ns
t_{HA}	Address Hold from Write End	0		0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	10		12		12		ns
t_{SD}	Data Set-Up to Write End	7		8		9		ns
t_{HD}	Data Hold from Write End	0		0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[6]	3		3		3		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[5, 6]		6		7		8	ns
t_{BW}	Byte Enable to End of Write	10		12		12		ns

Notes:

4. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
5. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
6. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
7. The internal write time of the memory is defined by the overlap of CE LOW, and WE LOW. CE and WE must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
8. The minimum write cycle time for Write Cycle No. 3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.

Switching Characteristics[4] Over the Operating Range (continued)

Parameter	Description	-20		-25		Unit
		Min.	Max.	Min.	Max.	
READ CYCLE						
t_{RC}	Read Cycle Time	20		25		ns
t_{AA}	Address to Data Valid		20		25	ns
t_{OHA}	Data Hold from Address Change	3		5		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		20		25	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		8		10	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z	0		0		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[5, 6]		8		10	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[6]	3		5		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[5, 6]		8		10	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		20		25	ns
t_{DBE}	Byte Enable to Data Valid		8		10	ns
t_{LZBE}	Byte Enable to Low Z	0		0		ns
t_{HZBE}	Byte Disable to High Z		8		10	ns
WRITE CYCLE[7, 8]						
t_{WC}	Write Cycle Time	20		25		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	13		15		ns
t_{AW}	Address Set-Up to Write End	13		15		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	13		15		ns
t_{SD}	Data Set-Up to Write End	9		10		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[6]	3		5		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[5, 6]		8		10	ns
t_{BW}	Byte Enable to End of Write	13		15		ns

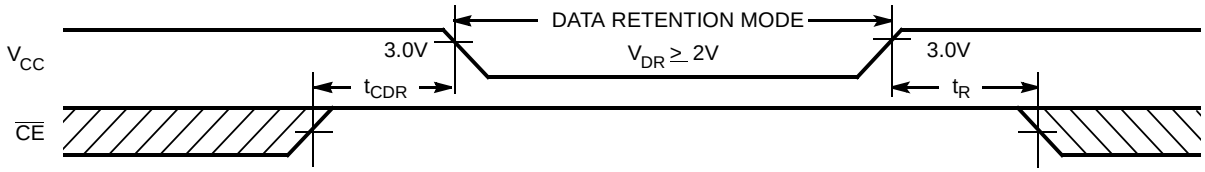
Data Retention Characteristics Over the Operating Range (For L version only)

Parameter	Description	Conditions[10]	Min.	Max.	Unit
V_{DR}	V_{CC} for Data Retention		2.0		V
I_{CCDR}	Data Retention Current	$\overline{V_{CC}} = V_{DR} = 2.0V$, $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$		330	µA
t_{CDR}[3]	Chip Deselect to Data Retention Time		0		ns
t_R[9]	Operation Recovery Time		t_{RC}		ns

Notes:

9. $t_r \leq 3$ ns for the -12 and -15 speeds. $t_r \leq 5$ ns for the -20 and slower speeds.
10. No input may exceed V_{CC} + 0.5V.

Data Retention Waveform



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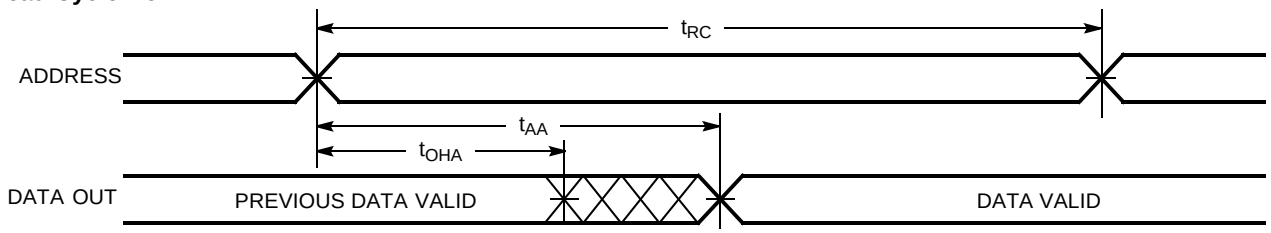
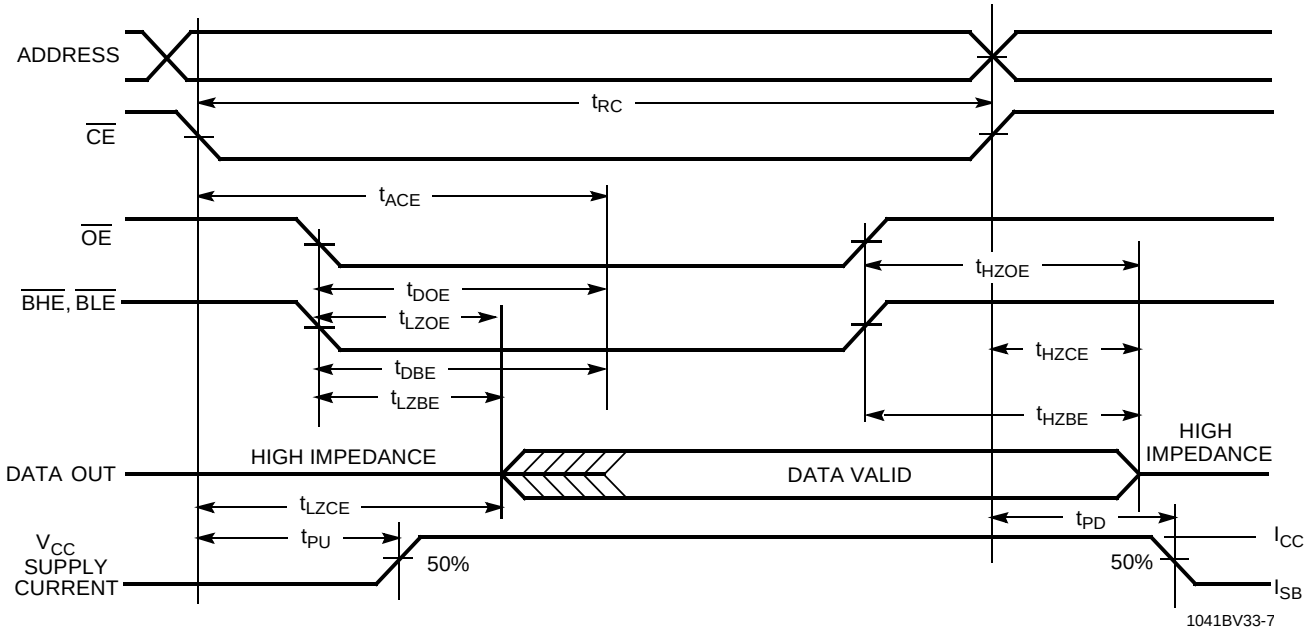
Switching Waveforms

Read Cycle No. 1 [11, 12]



1041BV33-6

Read Cycle No. 2 ($\overline{OE}$ Controlled) [12, 13]

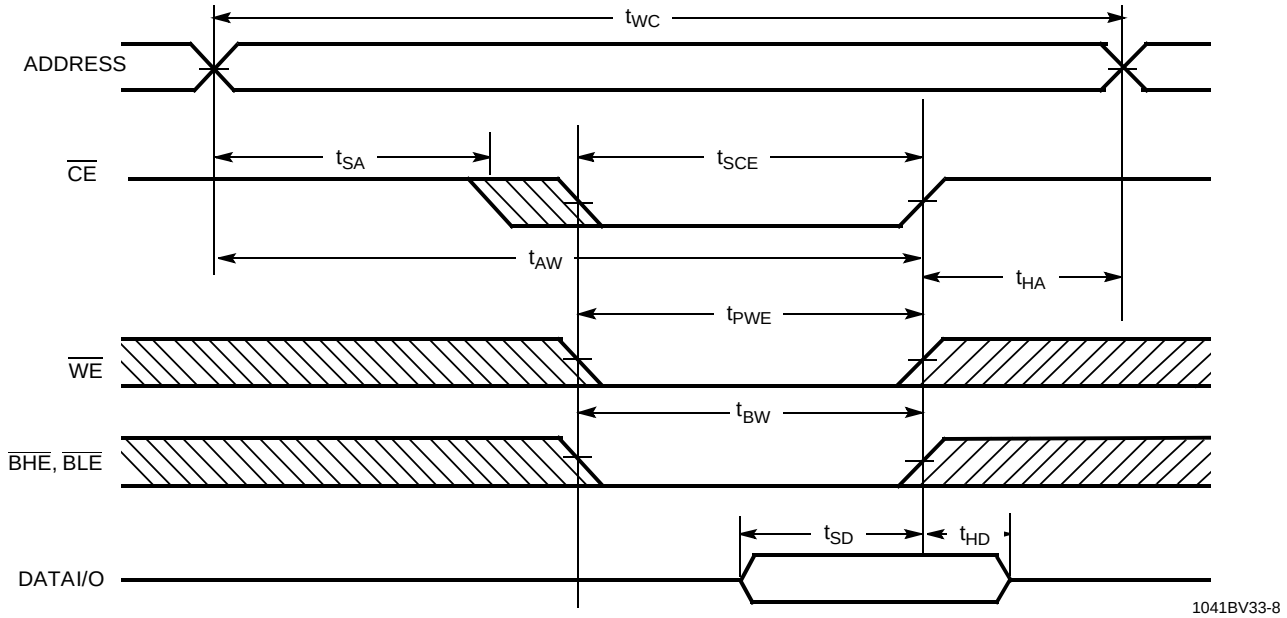


1041BV33-7

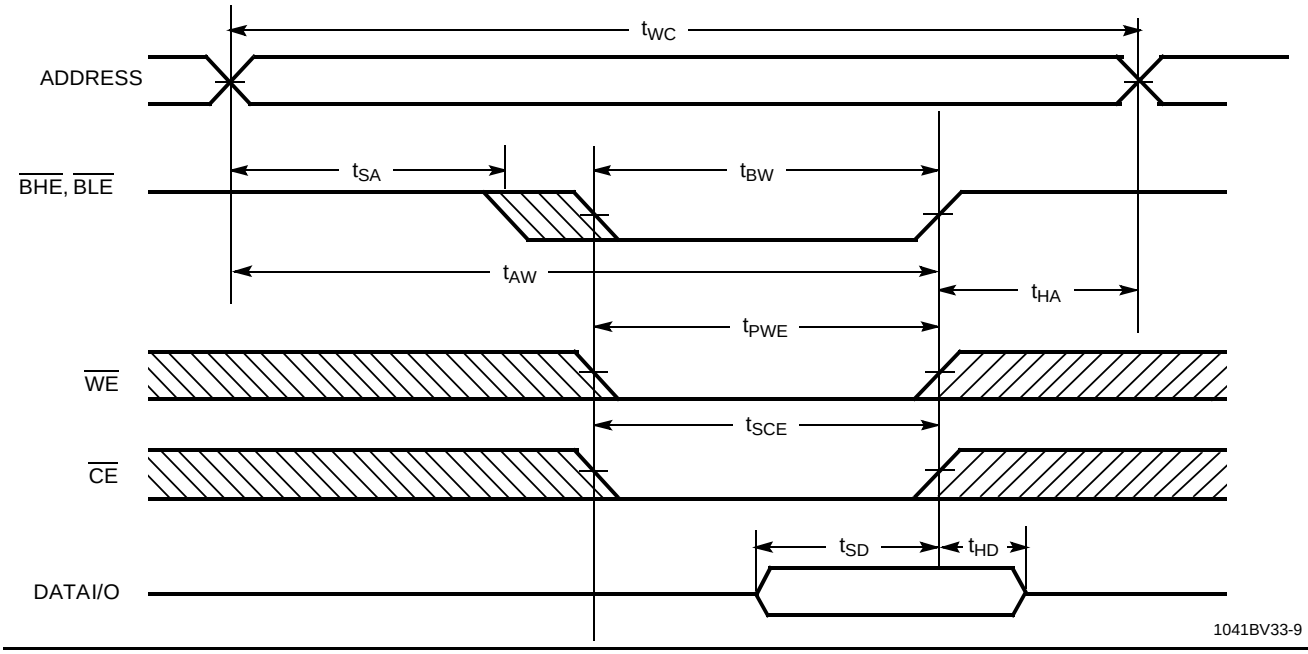
Notes:
11. Device is continuously selected. $\overline{OE}$, $\overline{CE}$, $\overline{BHE}$ and/or $\overline{BHE} = V_{IL}$.
12. $\overline{WE}$ is HIGH for read cycle.
13. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{CE}$ Controlled)[14, 15]



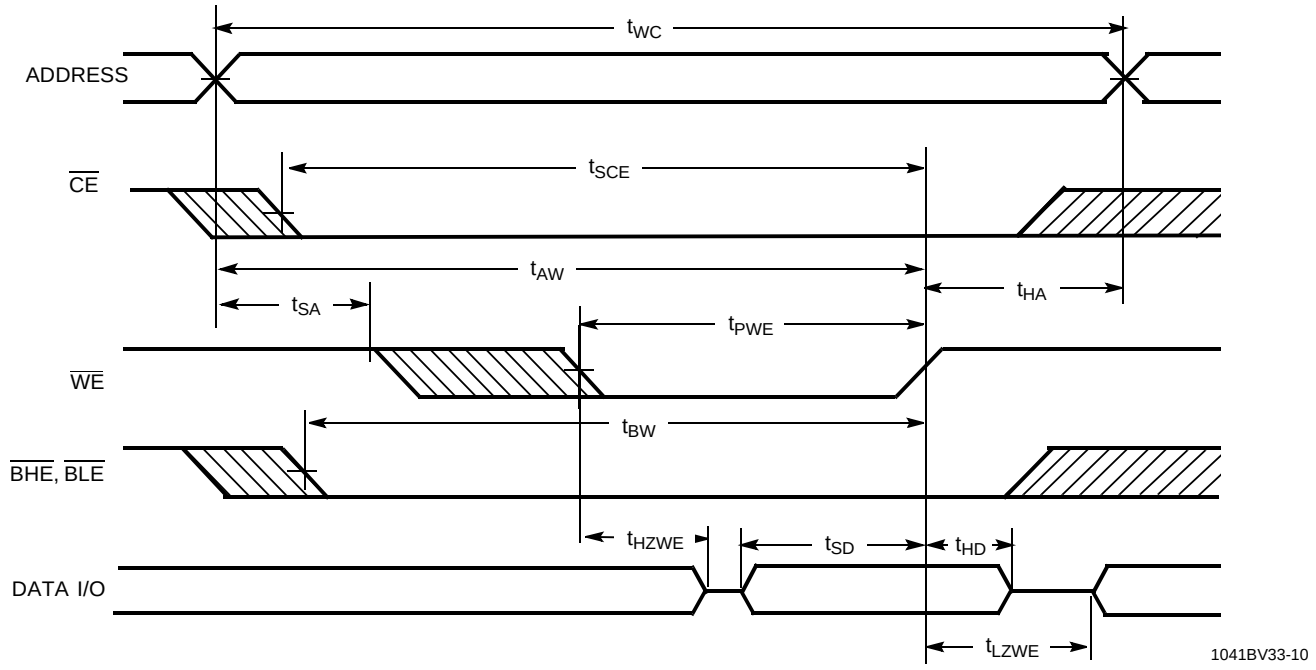
Write Cycle No. 2 ($\overline{BLE}$ or $\overline{BHE}$ Controlled)



Notes:
14. Data I/O is high-impedance if $\overline{OE}$ or $\overline{BHE}$ and/or $\overline{BLE}$= V_{IH}.
15. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH, the output remains in a high–impedance state.

Switching Waveforms (continued)

Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)



Truth Table

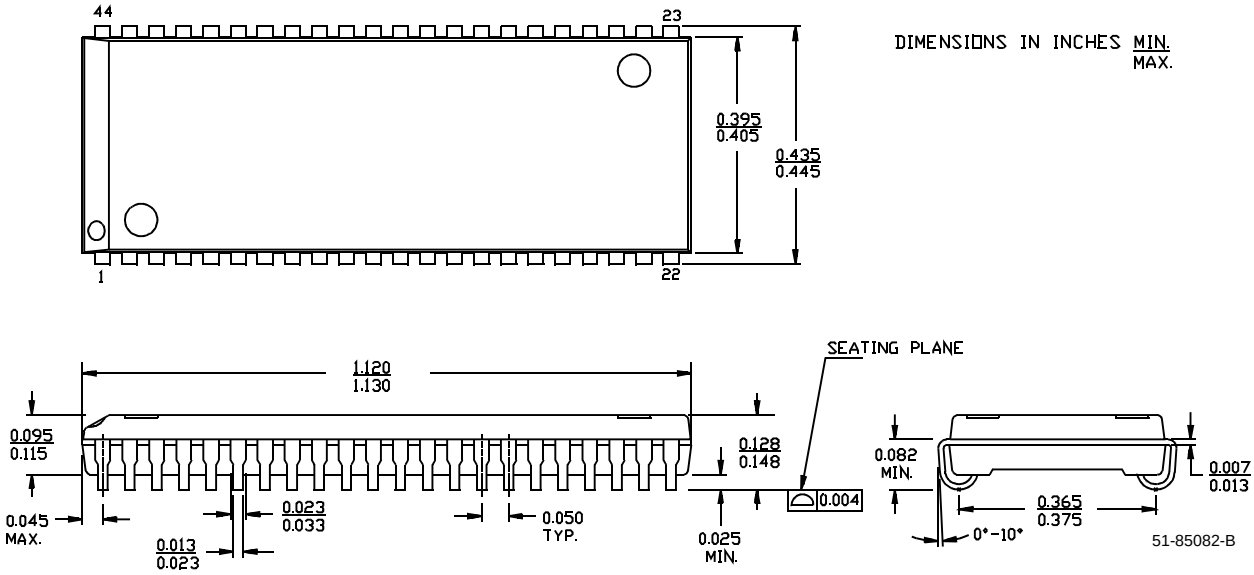
$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{BLE}$	$\overline{BHE}$	I/O_0–I/O_7	I/O_8–I/O_{15}	Mode	Power
H	X	X	X	X	High Z	High Z	Power Down	Standby (I_{SB})
L	L	H	L	L	Data Out	Data Out	Read All Bits	Active (I_{CC})
L	L	H	L	H	Data Out	High Z	Read Lower Bits Only	Active (I_{CC})
L	L	H	H	L	High Z	Data Out	Read Upper Bits Only	Active (I_{CC})
L	X	L	L	L	Data In	Data In	Write All Bits	Active (I_{CC})
L	X	L	L	H	Data In	High Z	Write Lower Bits Only	Active (I_{CC})
L	X	L	H	L	High Z	Data In	Write Upper Bits Only	Active (I_{CC})
L	H	H	X	X	High Z	High Z	Selected, Outputs Disabled	Active (I_{CC})

Ordering Information

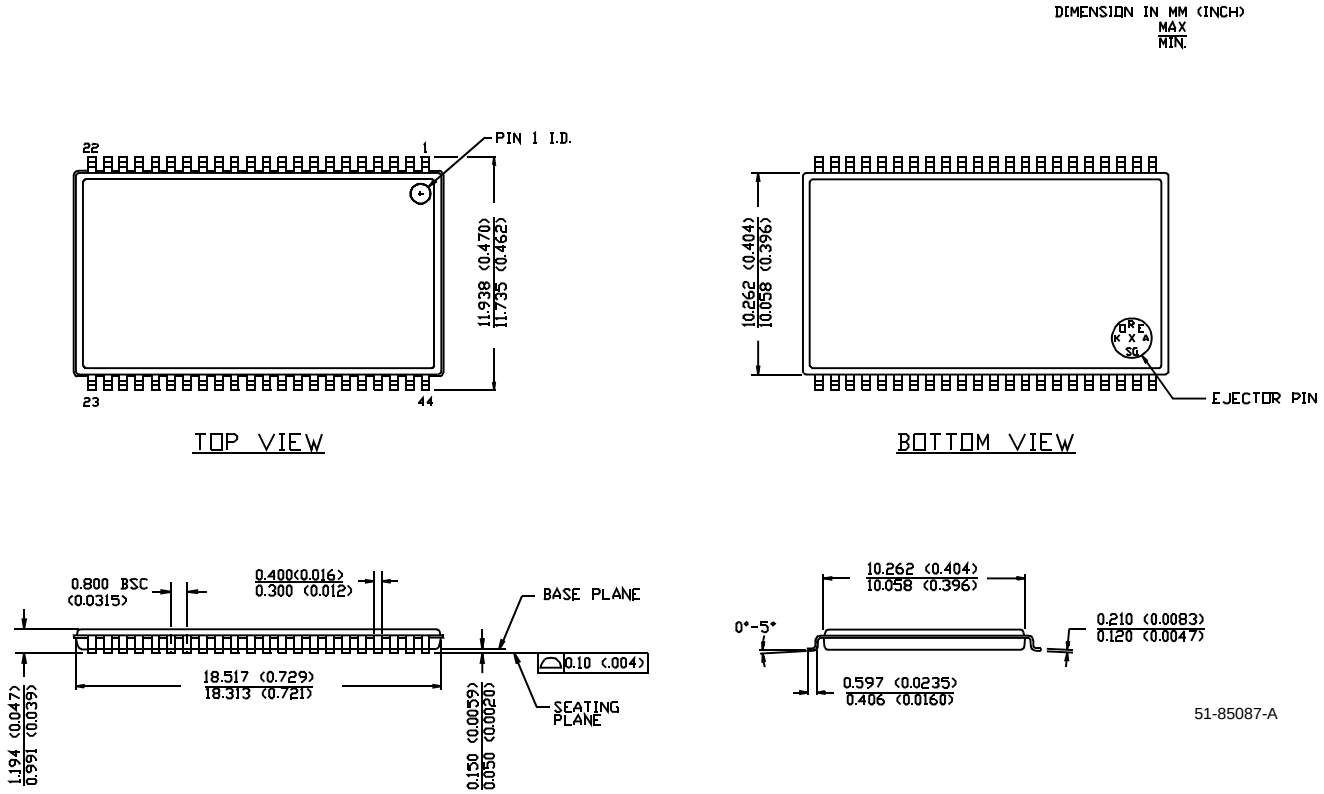
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
12	CY7C1041BV33-12VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-12VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-12ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-12ZC	Z44	44-Pin TSOP II Z44	
15	CY7C1041BV33-15VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-15VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-15ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-15ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33-15VI	V34	44-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1041BV33-15ZI	Z44	44-Pin TSOP II Z44	
17	CY7C1041BV33-17VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-17VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-17ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-17ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33-17VI	V34	44-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1041BV33-17ZI	Z44	44-Pin TSOP II Z44	
20	CY7C1041BV33-20VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-20VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-20ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-20ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33-20VI	V34	44-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1041BV33-20ZI	Z44	44-Pin TSOP II Z44	
25	CY7C1041BV33-25VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-25VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-25ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-25ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33-25VI	V34	44-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1041BV33-25ZI	Z44	44-Pin TSOP II Z44	

Package Diagrams

44-Lead (400-Mil) Molded SOJ V34



44-Pin TSOP II Z44



Document Title: CY7C1041BV33 256K x 16 SRAM Document Number: 38-05168				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	111840	11/17/01	DSG	Change from Spec number: 38-00932 to 38-05168